NSN 5961-01-102-8558

Transistor - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-102-8558 **Inclosure Material:** Metal **Overall Length:** 0.450 inches **Overall Diameter:** 0.875 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Internal Junction Configuration:** Pnp **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 90.0 breakdown voltage, collector-to-base, emitter open and 5.0 breakdown voltage, emitter-to-base, collector open and 90.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 15.00 amperes source cutoff current and 5.00 amperes source cutoff current **Power Rating Per Characteristic:** 125.0 watts small-signal input power, common-collector **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Terminal Type And Quantity:** 1 case and 2 uninsulated wire lead **Specification Data:** 80131-release6324 professional/industrial association specification Shelf Life: N/a **Unit Of Measure:**

Fiig: A110a0

No

Demilitarization: